



FIG. 1

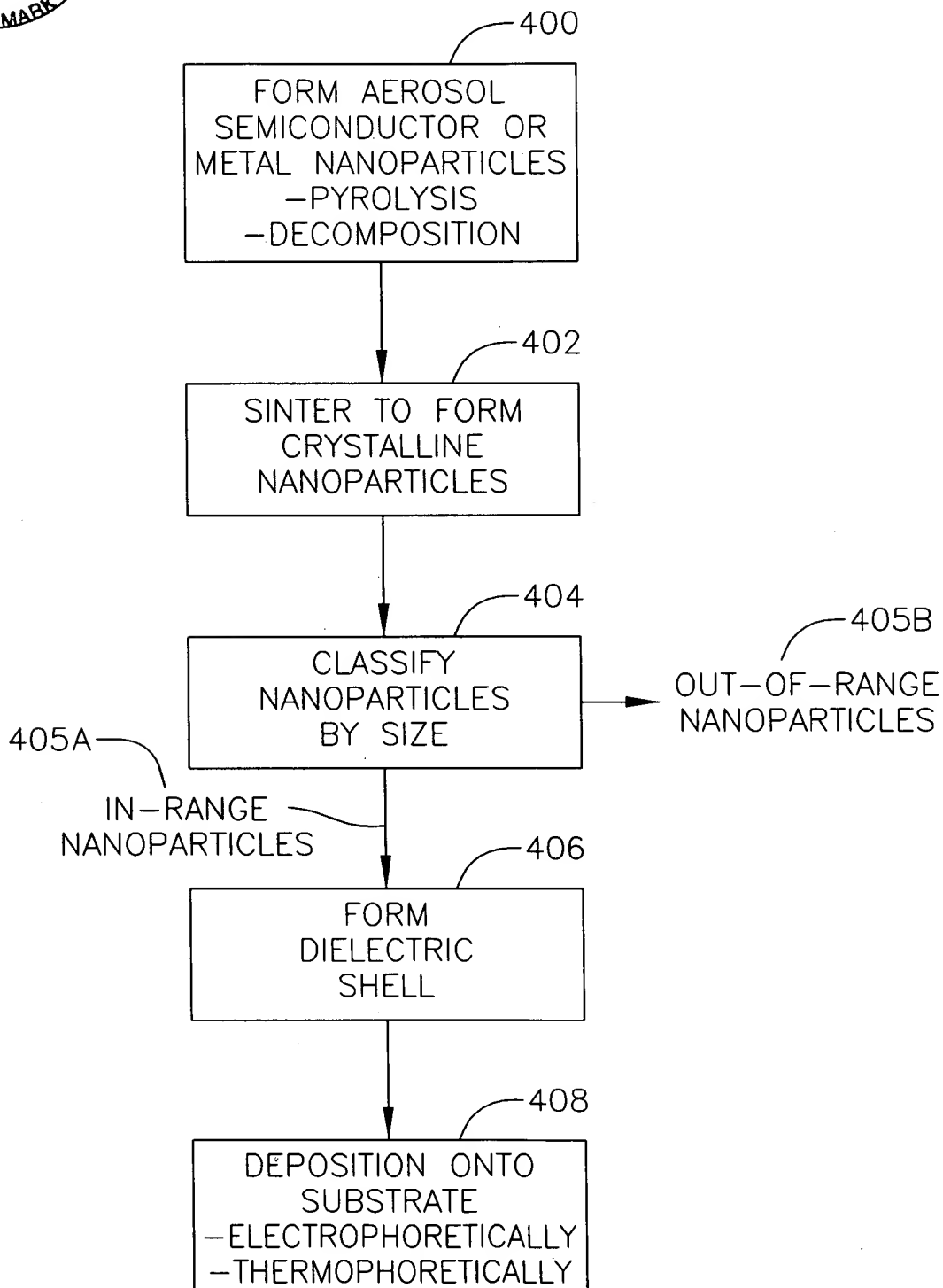


FIG. 2

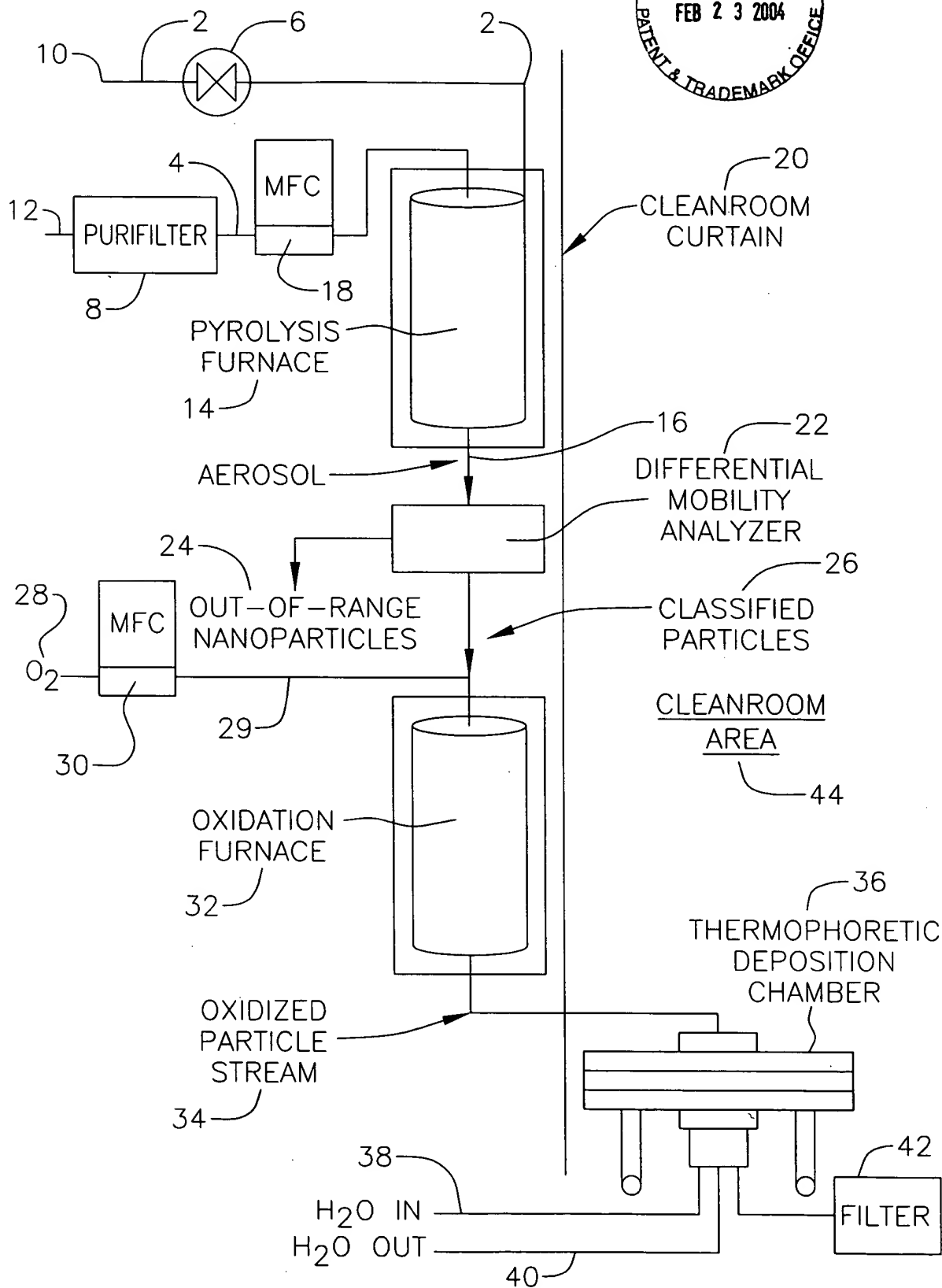




FIG. 3

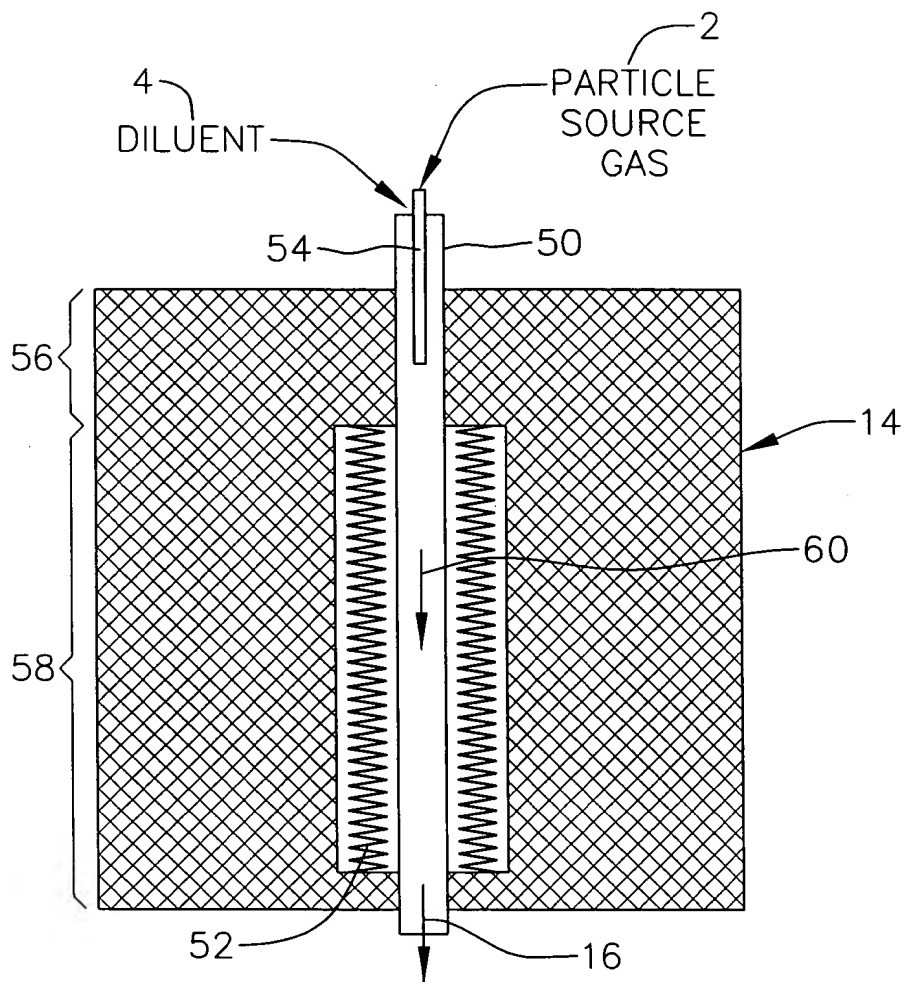
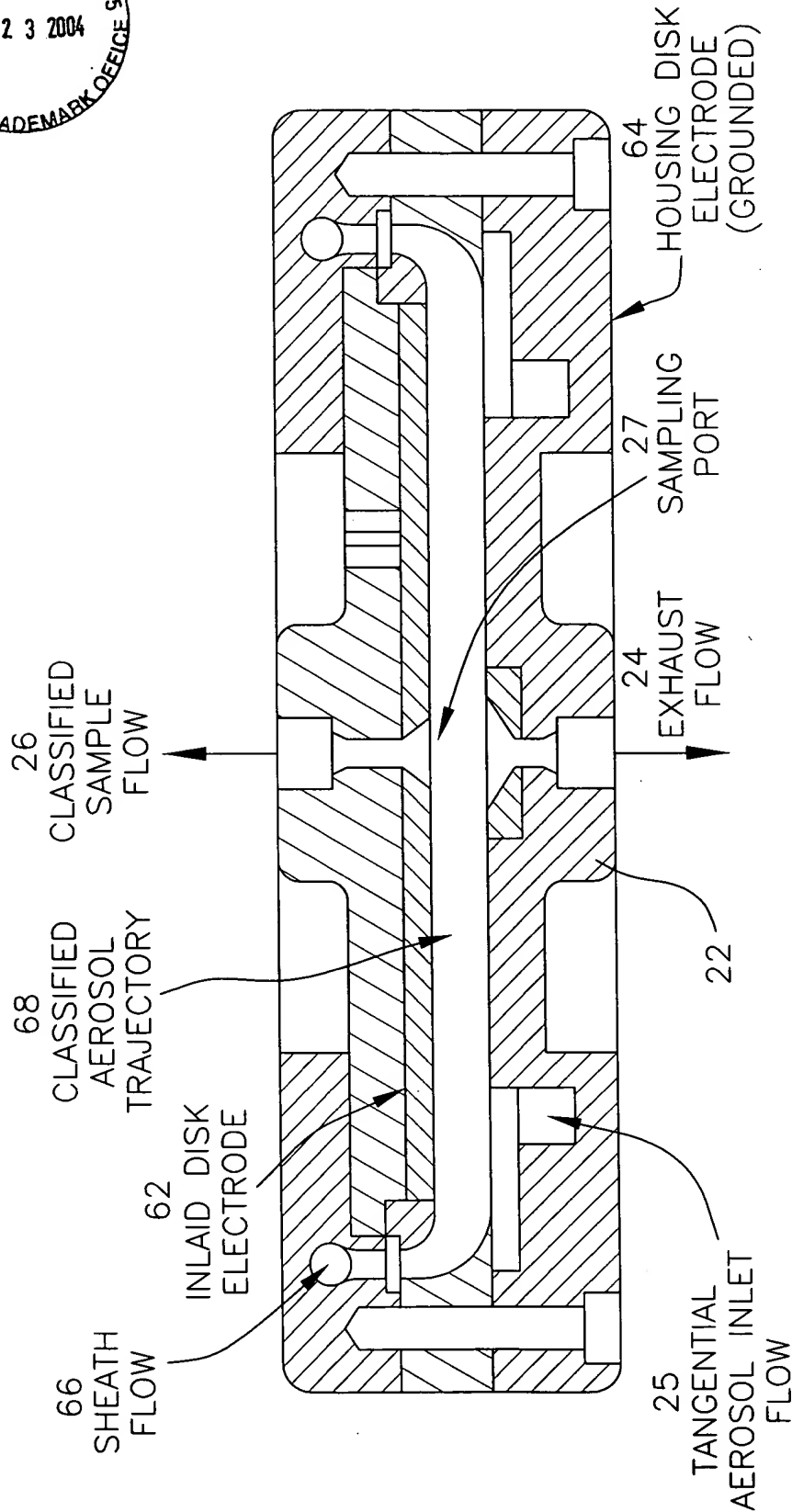




FIG. 4



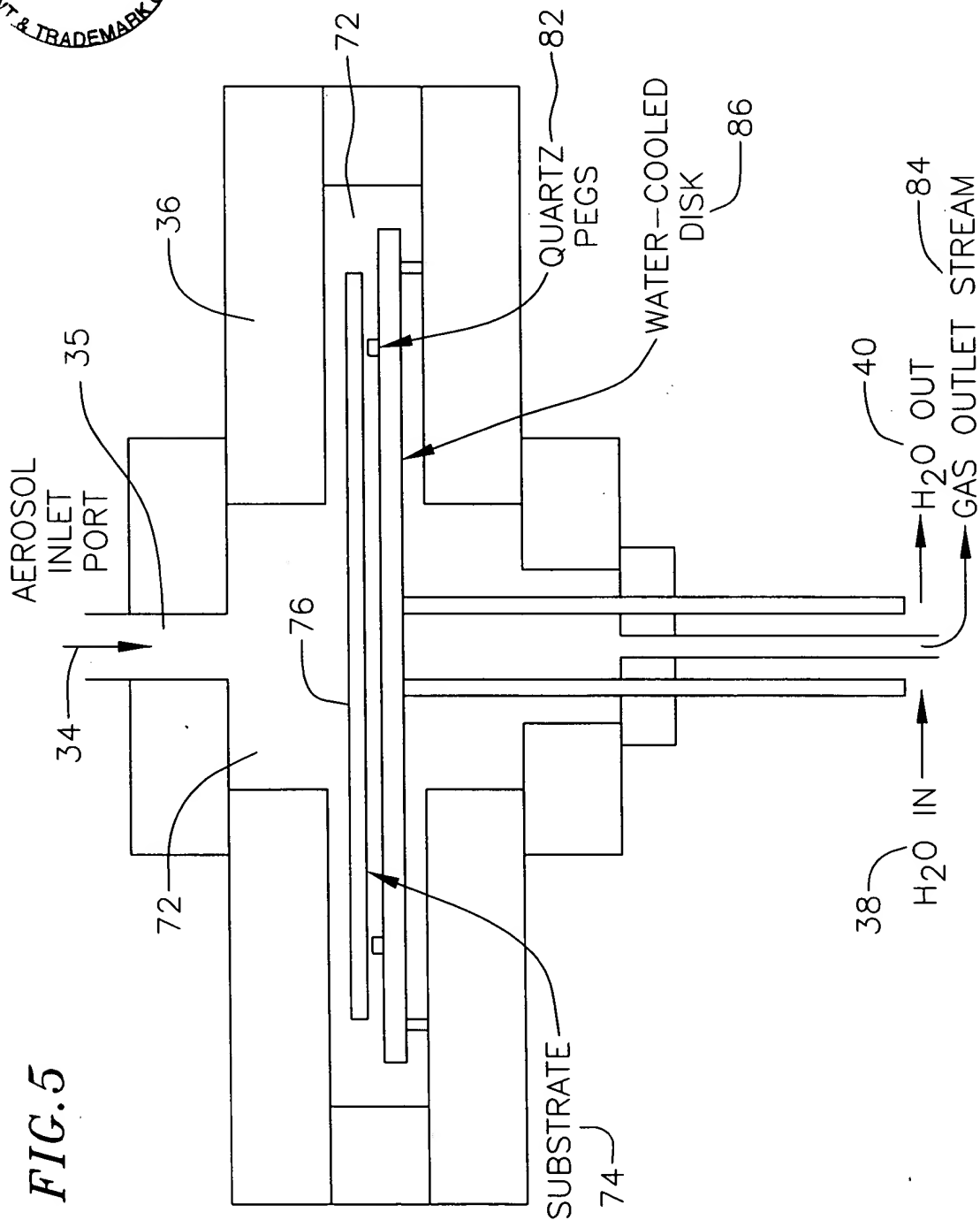




FIG. 6

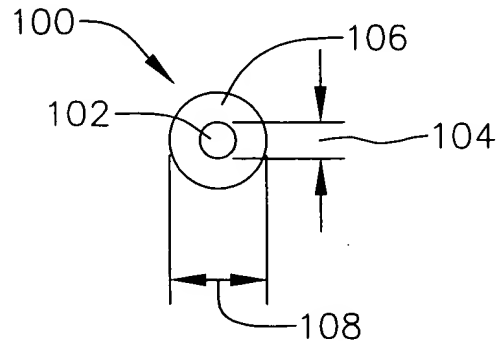


FIG. 7

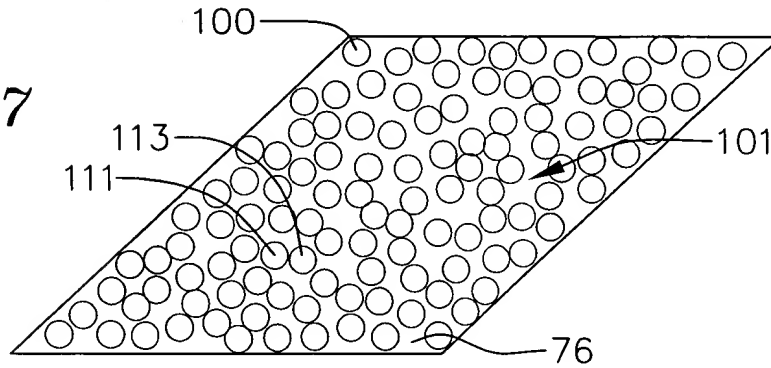


FIG. 8

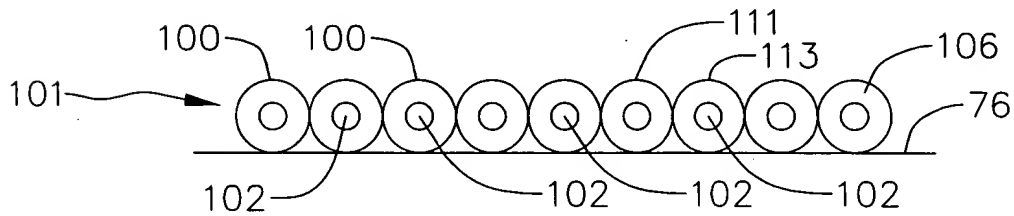


FIG. 9

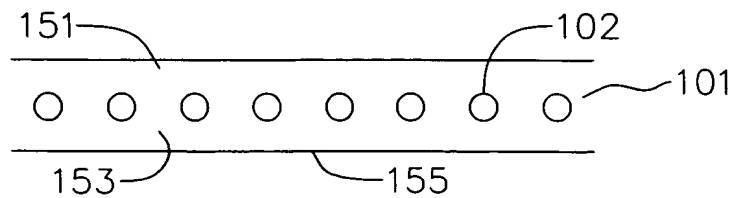




FIG. 10

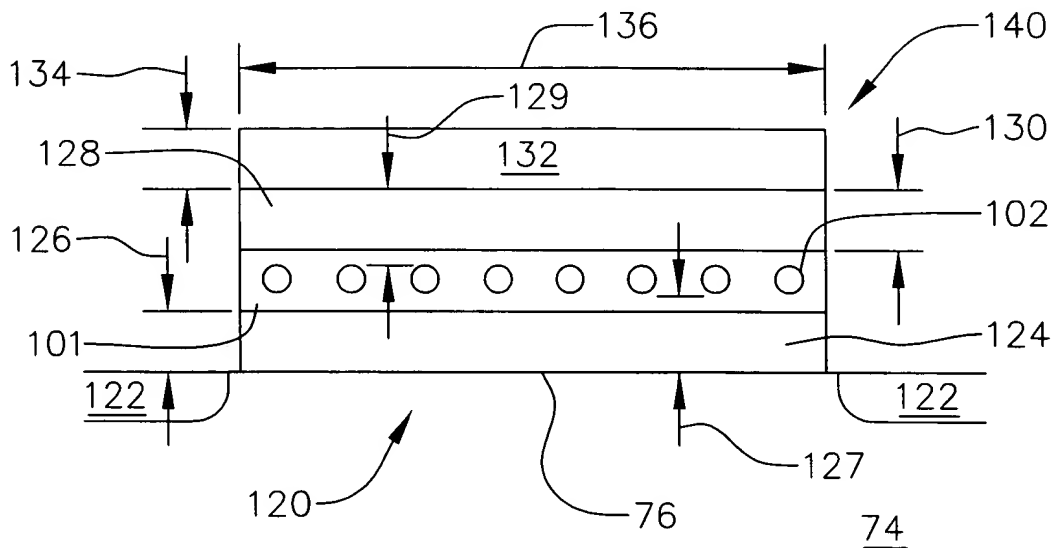


FIG. 11

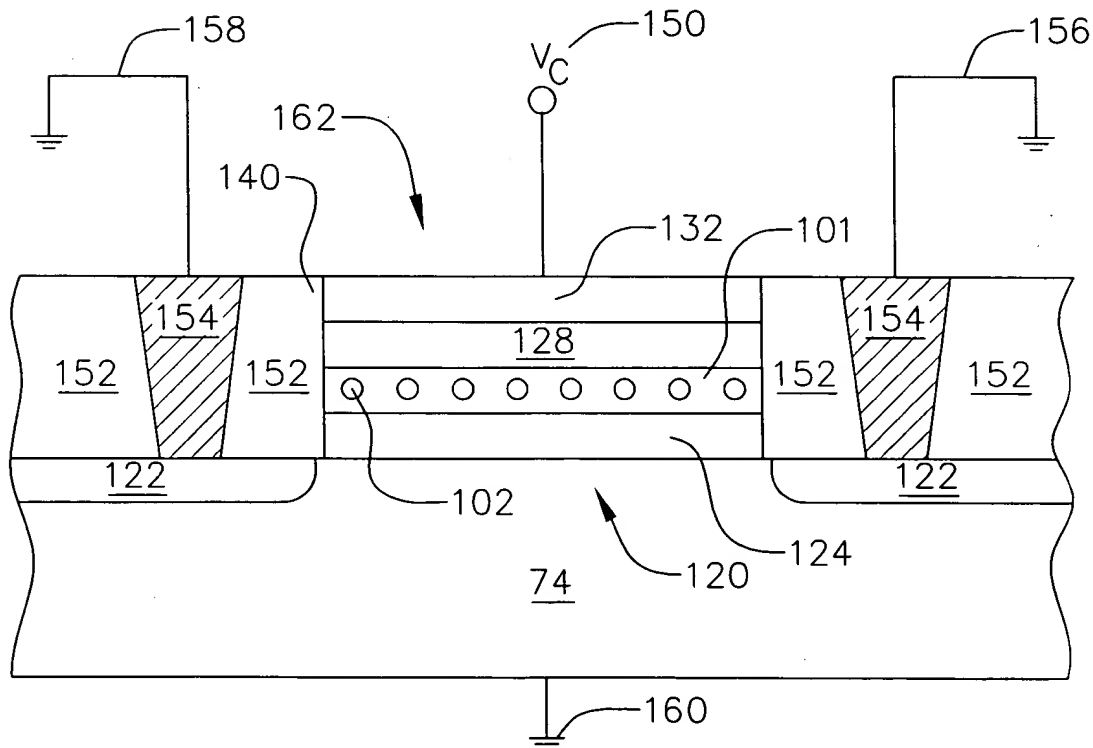
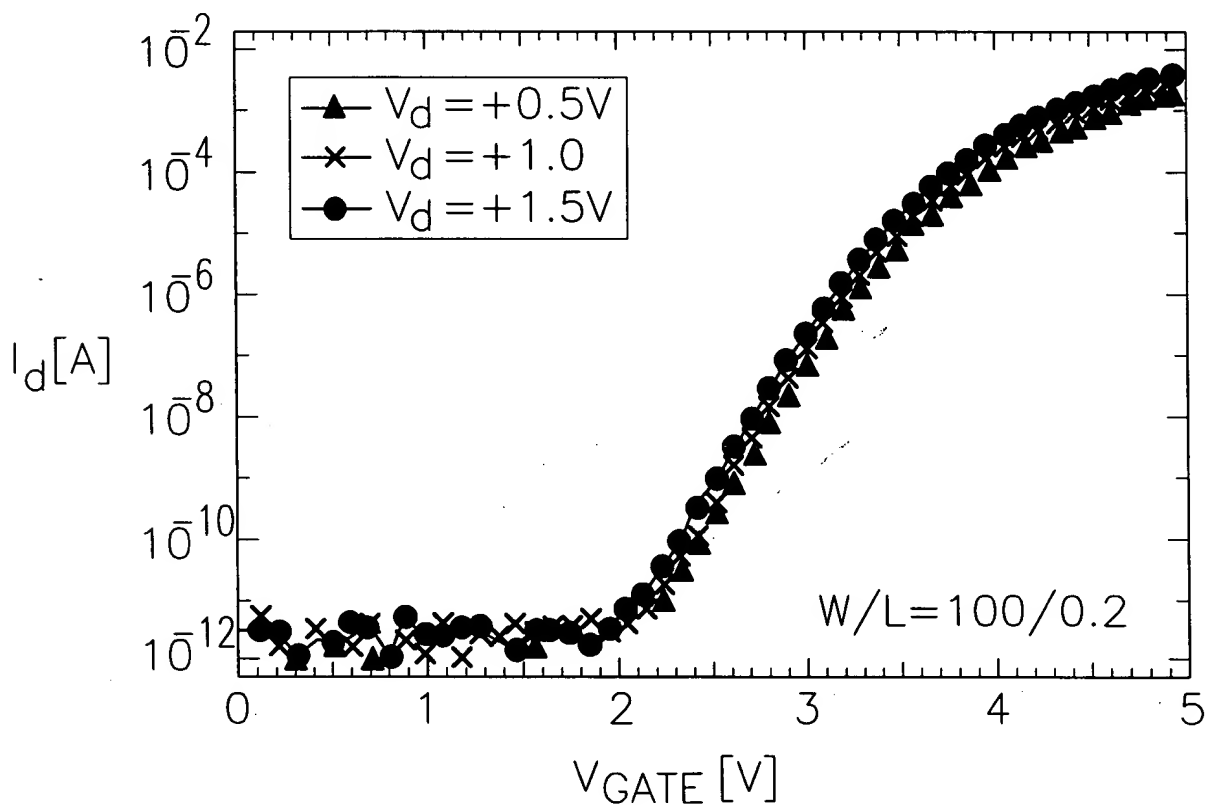
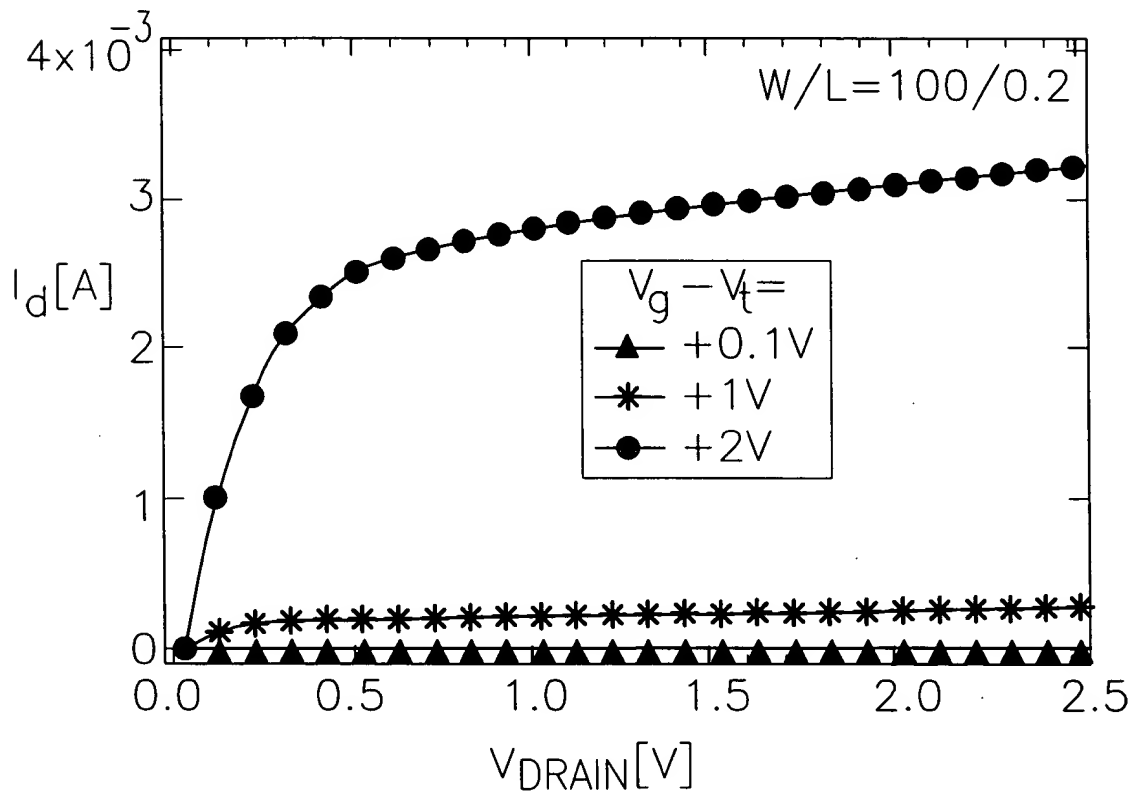




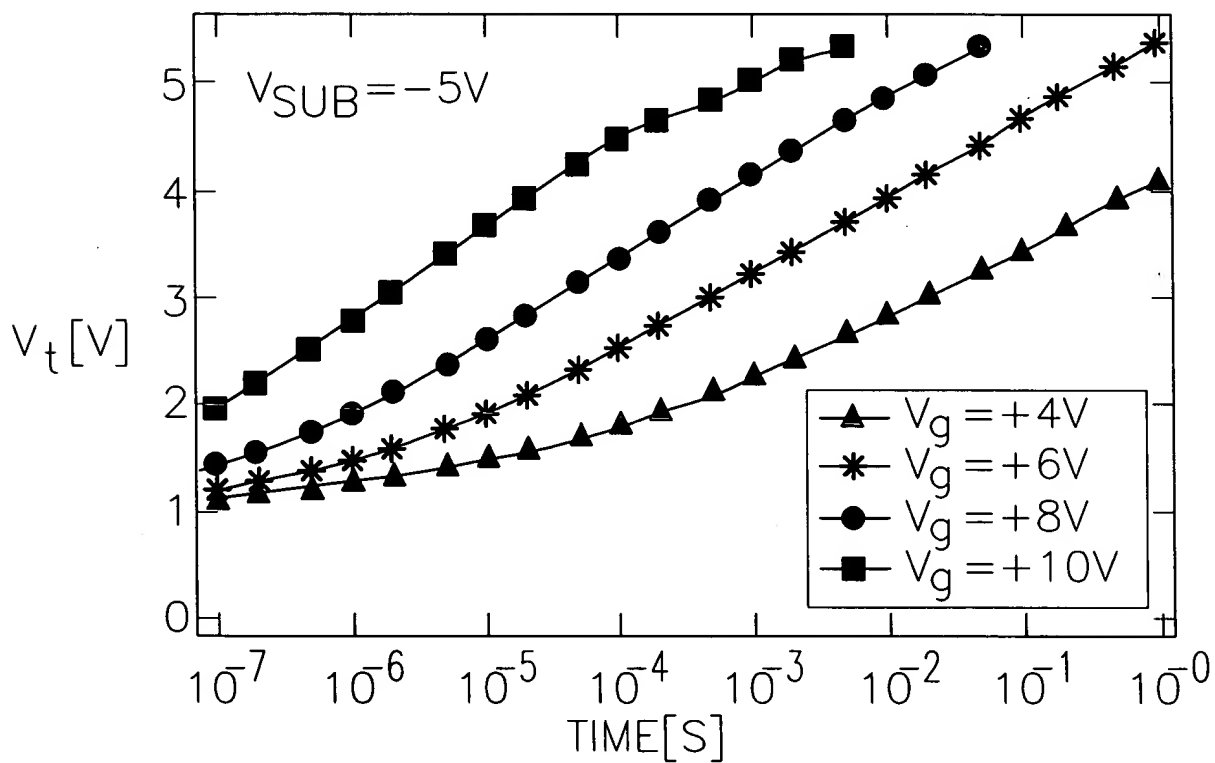
FIG. 12



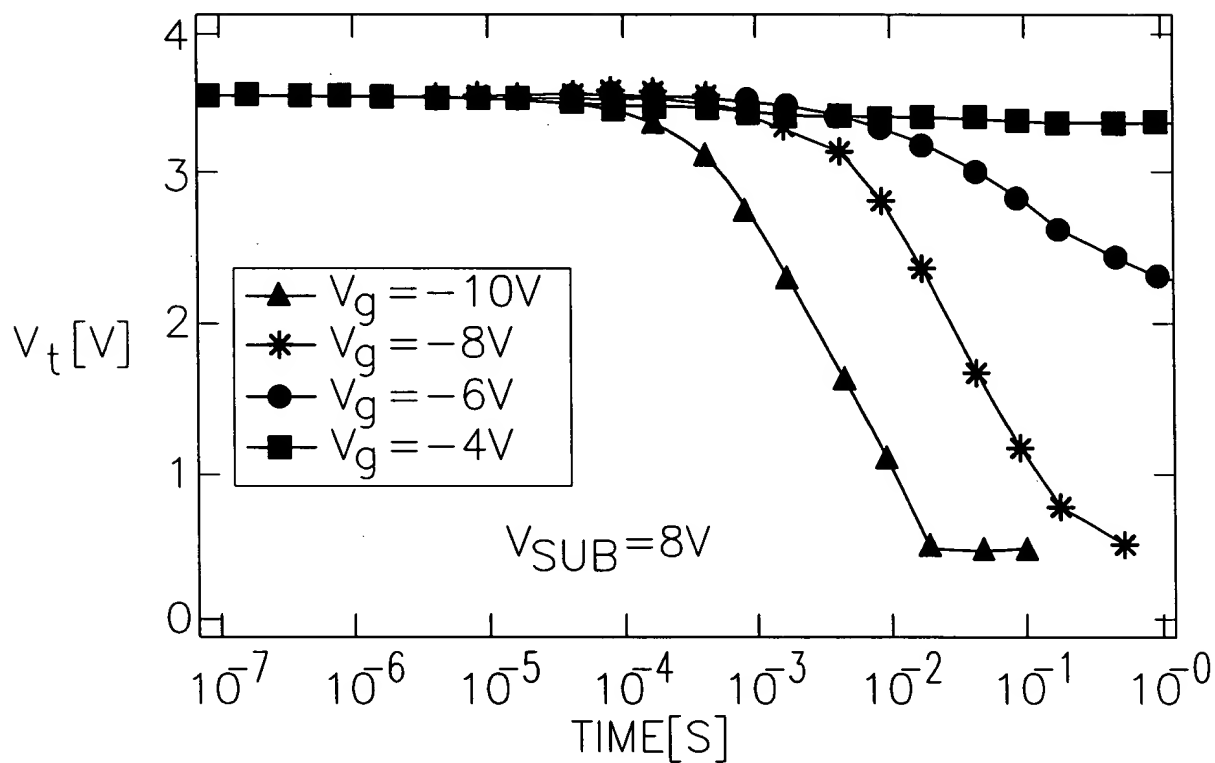
SUBTHRESHOLD CHARACTERISTICS OF A $0.2\mu\text{m}$ n-TYPE
AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET
(SUBTHRESHOLD SLOPE=200mV/dec; DIBL=100mV/V).

*FIG. 13*

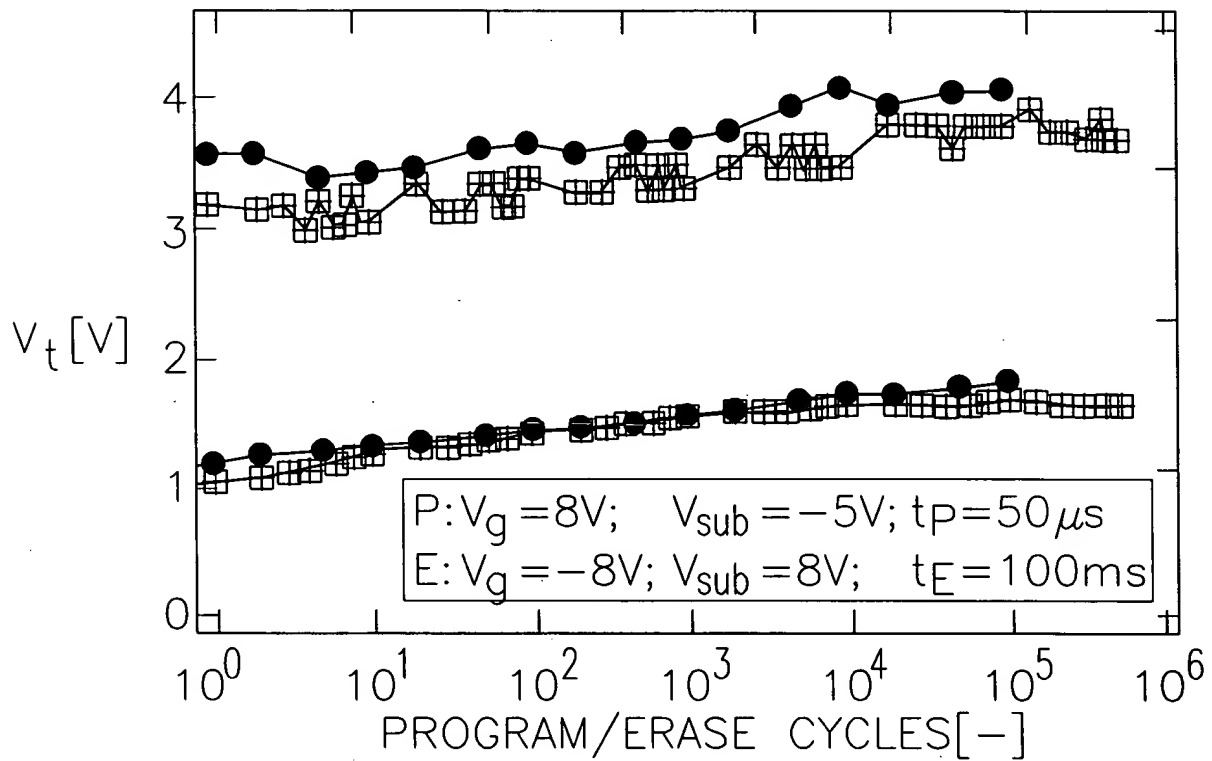
OUTPUT CHARACTERISTICS OF A $0.2\mu m$
AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET;
DRIVE CURRENT = $30\mu A/\mu m$

*FIG. 14*

PROGRAMMING TRANSIENTS (UNIFORM FN
TUNNELING) OF THE NANOCRYSTAL NVM DEVICE.

*FIG. 15*

ERASE TRANSIENTS (UNIFORM FN TUNNELING).

*FIG. 16*

ENDURANCE CHARACTERISTIC; ONLY LIMITED WINDOW CLOSURE IS OBSERVED AFTER 10^5 PROGRAM/ERASE CYCLES.



FIG. 17

